B-KUL-H05E3A Design Project

Switched-Capacitor Amplifier Specification table

Group	f _s	SNR _{min}	ε gain	ε _{set}	PM _{min}	C _L	V _{in}	A _{CL}	Input
#	[MHz]	[dB]	[%]	[%]	[°]	[pF]	[mV _{pp}]	[V/V]	pair
1	50	45	0.04	2	60	2	50~100	10	pMOS
2	50	45	0.05	2.2	60	2	50~100	10	nMOS
3	55	45	0.05	2.4	60	2	50~100	10	pMOS
4	55	45	0.06	2.6	60	2	50~100	10	nMOS
5	60	45	0.06	2.8	60	2	50~100	10	pMOS
6	60	45	0.07	3.0	60	2	50~100	10	nMOS
7	65	45	0.07	3.2	60	2	50~100	10	pMOS
8	65	45	0.04	5	60	2	50~100	10	nMOS
9	70	45	0.04	5.2	60	2	50~100	10	pMOS
10	70	45	0.05	5.4	60	2	50~100	10	nMOS
11	75	45	0.05	5.6	60	2	50~100	10	pMOS
12	75	45	0.06	5.8	60	2	50~100	10	nMOS
13	80	45	0.06	6.0	60	2	50~100	10	pMOS
14	80	45	0.07	6.2	60	2	50~100	10	nMOS
15	50	47	0.06	3	60	2.5	50~100	10	pMOS
16	50	47	0.07	3.2	60	2.5	50~100	10	nMOS
17	55	47	0.07	3.4	60	2.5	50~100	10	pMOS
18	55	47	0.08	3.6	60	2.5	50~100	10	nMOS
19	60	47	0.08	3.8	60	2.5	50~100	10	pMOS
20	60	47	0.09	4	60	2.5	50~100	10	nMOS
21	65	47	0.09	4.2	60	2.5	50~100	10	pMOS
22	65	47	0.06	5	60	2.5	50~100	10	nMOS
23	70	47	0.06	5.2	60	2.5	50~100	10	pMOS
24	70	47	0.07	5.4	60	2.5	50~100	10	nMOS
25	75	47	0.07	5.6	60	2.5	50~100	10	pMOS
26	75	47	0.08	5.8	60	2.5	50~100	10	nMOS
27	<mark>80</mark>	47	0.08	6.0	60	2.5	50~100	10	pMOS
28	80	47	0.09	6.2	60	2.5	50~100	10	nMOS
29	80	42	0.06	2.2	60	1.5	50~100	10	nMOS
30	50	42	0.06	2.4	60	1.5	50~100	10	pMOS
31	50	42	0.07	2.6	60	1.5	50~100	10	nMOS
32	55	42	0.06	2.8	60	1.5	50~100	10	pMOS
33	55	42	0.07	3.0	60	1.5	50~100	10	nMOS

f s	Sampling frequency					
SNR _{min}	Output signal to noise ratio @minimum input swing (i.e., 50mV _{pp})					
ε _{gain}	Static gain error					
€ set	Dynamic settling error					
PM _{min}	Minimum phase margin in worst case (i.e., unity-gain feedback)					
CL	Load capacitor					
V _{in}	Peak-to-peak differential input swing (Note: amplitude is 25~50mV)					
A _{CL}	Magnitude of closed-loop gain at low frequencies					